

## A 4-V<sub>ppd</sub> 160-Gb/s PAM-4 Optical Modulator Driver with All-Pass Filter-Based Dynamic Bias and 2-Tap FFE

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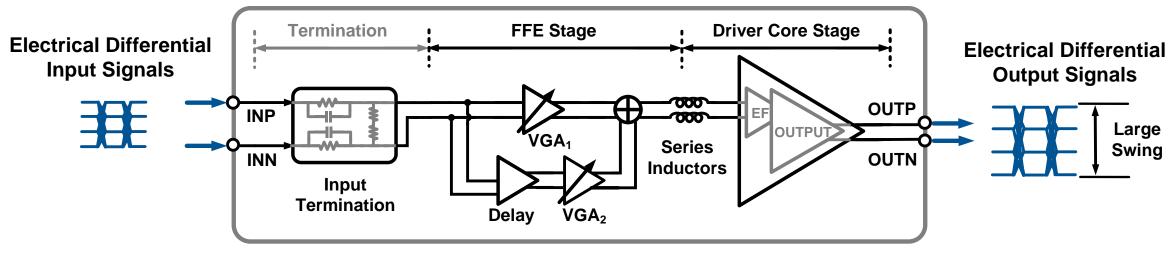
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## **Driver Circuit Implementation**



## A 4-V<sub>ppd</sub>160-Gb/s PAM-4 Optical Modulator Driver with All-Pass Filter-Based Dynamic Bias and 2-Tap FFE

- □Input Termination (passive EQ, improve BW)
- □FFE Stage (2-Tap, Re-configurable)
- □ Driver Core Stage (APF-based bias, BV Doubler)



Block diagram of the proposed electrical driver.

## **FFE Stage**



# Optical Modulator Driver with All-Pass Filter-Based Dynamic Bias and 2-Tap FFE

**FFE Stage** 

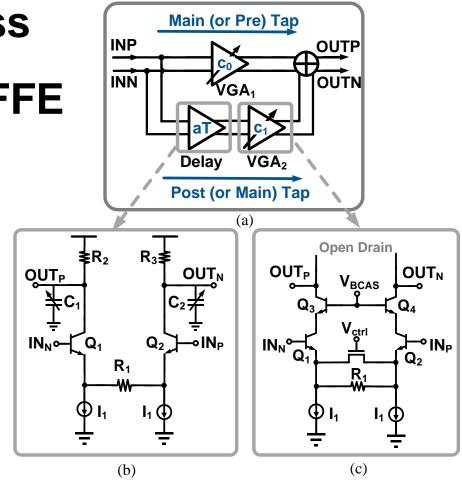
□1 Delay Cell

□2 VGAs

The EQ stage incorporates a 1

Fractional-Spaced ② 2-Tap FFE

and can be ③ re-configurable.



(a) Block diagram of 2-tap fractional-spaced feed-forward equalizer (FFE). (b) Schematic of the delay cell. (c) Schematic of the variable-gain amplifiers (VGAs).

## **Driver Core Stage**

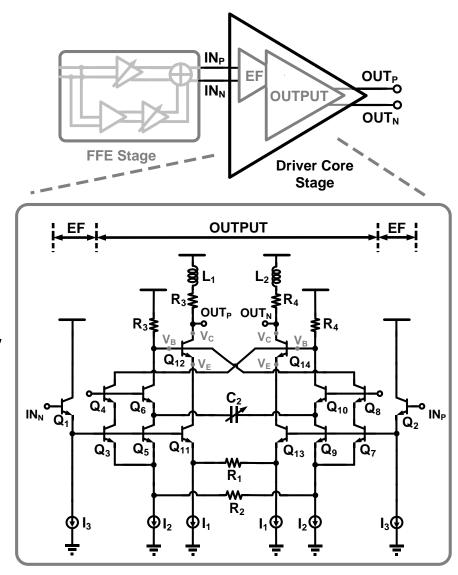


## Optical Modulator Driver with All-Pass Filter-Based Dynamic Bias and 2-Tap FFE

## **Driver Core Stage**

- □EF Stage
  - □Buffer & DC common-mode level shifter
- **□**Output Stage
  - **DAPF-based bias circuit**

$$H(j\omega\tau) = G \cdot \frac{1 - j\omega\tau}{1 + j\omega\tau} = G \cdot \left(\frac{2}{1 + j\omega\tau} - 1\right)$$



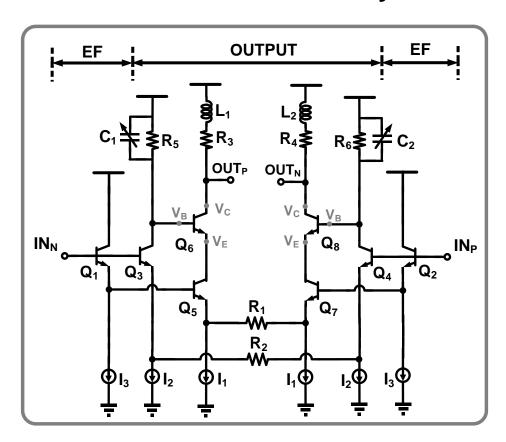
Schematic of the proposed BV doubler topology driver core with allpass filter (APF)-based bias.

## Comparison Between LPF and APF Driver Core Sulfstran University of Science and Section Conference on the Comparison Between LPF and APF Driver Core Sulfstrand Section Conference on the Comparison Between LPF and APF Driver Core Section Conference on the Comparison Between LPF and APF Driver Core Section Conference on the Core Section Core Section



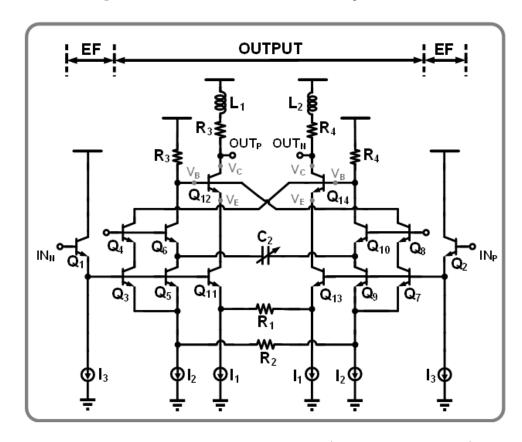
## **Output Stage: Dynamic Bias**

☐ Conventional LPF-based dynamic bias



$$H(j\omega) = \frac{G}{1 + j\omega \tau}$$

**Proposed APF-based dynamic bias** 

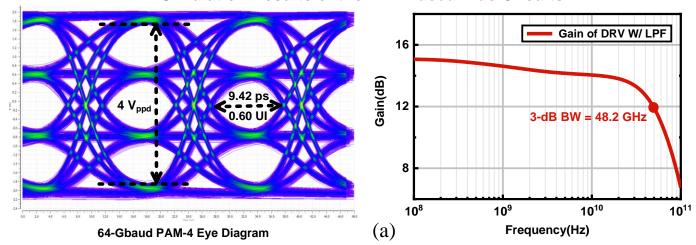


$$H(j\omega) = G \cdot \frac{1 - j\omega\tau}{1 + j\omega\tau} = G \cdot \left(\frac{2}{1 + j\omega\tau} - 1\right)$$

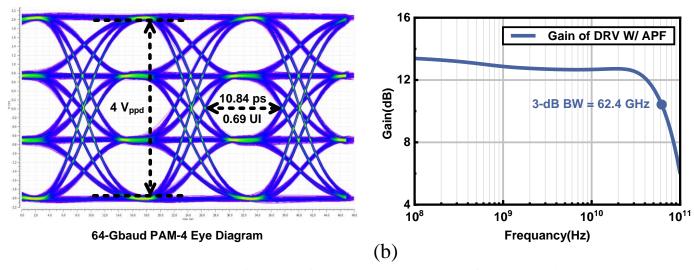
## **Comparison Between LPF and APF Driver Core**







#### Simulation Results of the APF-Based Bias Circuits



(a) 64-Gbaud PAM-4 eye diagram (left) and the frequency response (right) of the driver with LPF-based bias circuit. (b) 64-Gbaud PAM-4 eye diagram (left) and the frequency response (right) of the driver with APF-based bias circuit.

#### **Comparison Between**

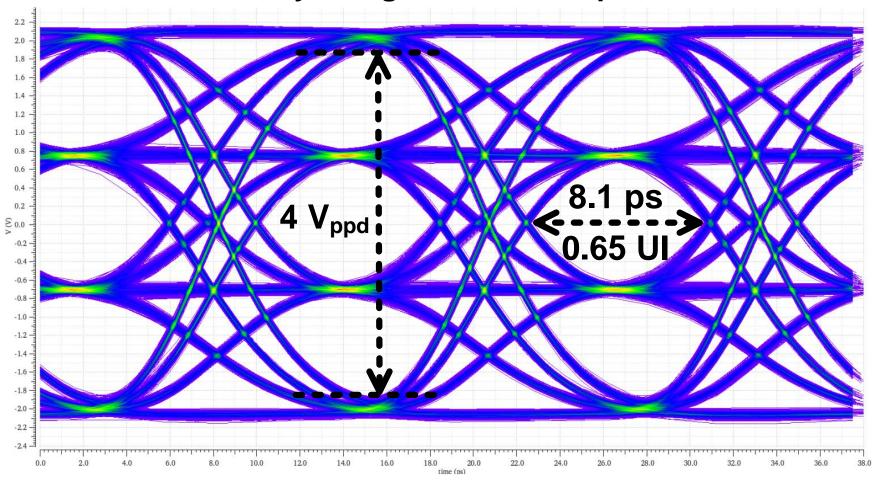
#### **LPF & APF versions**

|                            | LPF<br>Version          | APF<br>Version     |  |  |
|----------------------------|-------------------------|--------------------|--|--|
| Bandwidth                  | 48.2 GHz                | 62.4 GHz           |  |  |
| Ratio of Level<br>Mismatch | 91.2%                   | 95.1%              |  |  |
| Eye Width                  | 0.60 UI                 | 0.69 UI            |  |  |
| Power Consumption          | Close Power Consumption |                    |  |  |
| Output<br>Voltage          | 4 V <sub>ppd</sub>      | 4 V <sub>ppd</sub> |  |  |

## **Simulation Result**



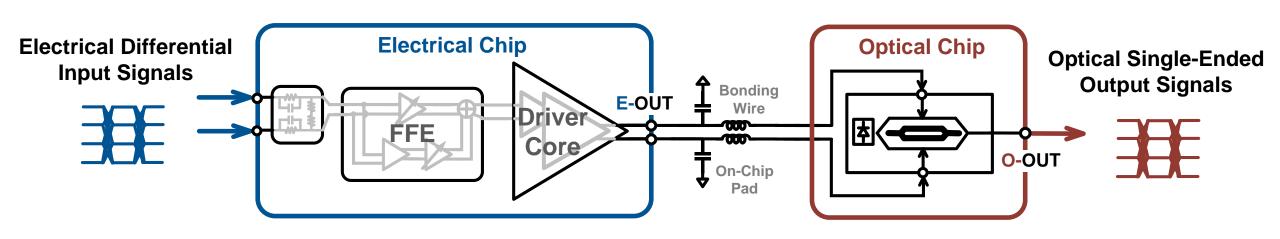




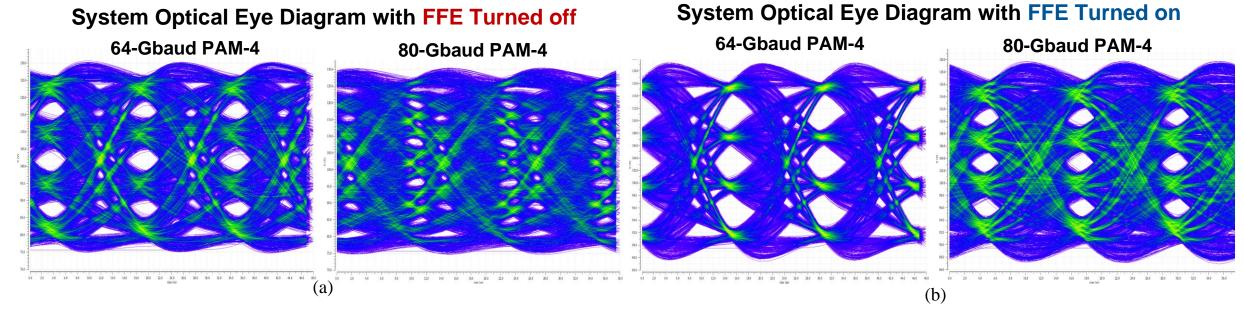
80-Gbaud PAM-4 eye diagram of the proposed driver.

## **E/O System Simulation Results**





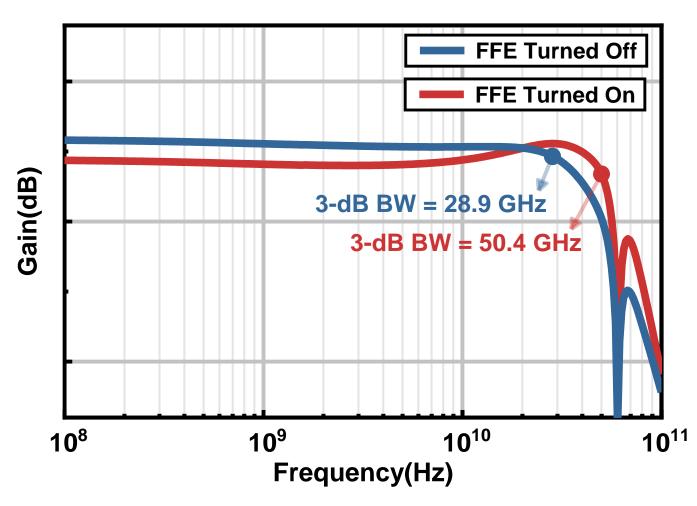
Electrical/optical (E/O) system with the proposed electrical driver and the optical MZM modulator.



(a) 64-Gbaud PAM-4 (left) and 80-Gbaud PAM-4 (right) E/O system optical eye diagram with FFE turned off. (b) 64-Gbaud PAM-4 (left) and 80-Gbaud PAM-4 (right) E/O system optical eye diagram with FFE turned on.

## **E/O System Simulation Results**





Simulated frequency response of the E/O system with FFE turned off and turned on.

## **Comparison Table**



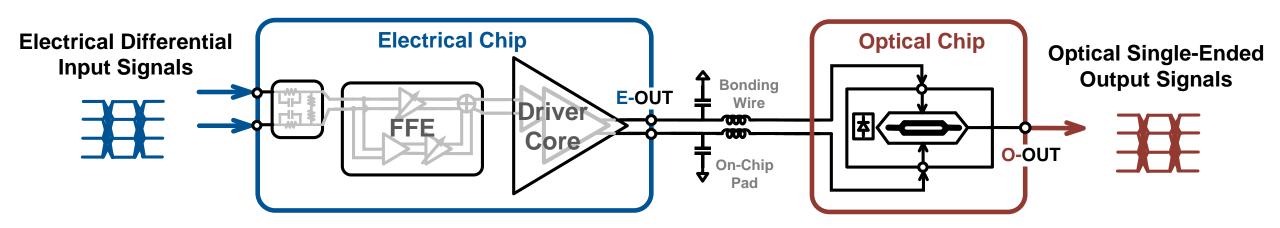
#### **Comparison Table with State of The Art**

|                                      | [1]                      | [2]                | [3]                     | [4]                     | [5]                   | This Work                |
|--------------------------------------|--------------------------|--------------------|-------------------------|-------------------------|-----------------------|--------------------------|
| TECHNOLOGY                           | 130-NM<br>SIGE<br>BICMOS | 250-NM<br>INP DHBT | 55-NM<br>SIGE<br>BICMOS | 55-NM<br>SIGE<br>BICMOS | 65-NM<br>CMOS         | 130-NM SIGE<br>BICMOS    |
| DIFFERENTIA<br>L OUTPUT<br>SWING (V) | 2.4<br>@PAM-4            | 1.8<br>@PAM-4      | 4.8<br>@PAM-4           | 4.4<br>@PAM-4           | 1.5<br>@PAM-<br>4     | 4 @PAM-4                 |
| ELECTRICAL<br>BW (GHz)               | > 40                     | 67                 | 57.5                    | > 70                    | 48                    | 62                       |
| E/O BW<br>(GHz)                      | 40                       | N.A.               | N.A.                    | N.A.                    | 43                    | 50.4                     |
| DATA RATE<br>(GB/S)                  | 552 @<br>DP-<br>16QAM    | 112 @<br>PAM-4     | 128 @<br>PAM-4          | 128 @<br>PAM-4          | 640 @<br>DP-<br>32QAM | 160 @ PAM-<br>4          |
| GAIN @ 1<br>GHz                      | 20-30                    | 1-11               | 12.8                    | 20                      | 13-22.5               | 13.4                     |
| Power (W)                            | 4                        | 0.84               | 0.82                    | 1.1                     | 0.9                   | 1.15 (DRIVER CORE: 0.99) |



## Some Re-Thinking about the Issues Mentioned Last Week

About How Bonding Wire Transmit High-Speed Signals?



Electrical/optical (E/O) system with the proposed electrical driver and the optical MZM modulator.

## **Some Thinking**



**Output Signals** 

## About How Bonding Wire Transmit High-Speed Signals?

- ☐ Using the empirical value of boning wire (300pH) in simulations indicates that the high-speed transmission is possible.
- ☐ Make the wire as short as possible such as by PCB digging slots, so that the electrical chip and MZM optical chip the same height.
- ☐ The bonding wire will actually cause the bandwidth reduction, which can be compensated by EQ (FFE) stage.
- ☐ In the future, use relatively more advanced packaging methods such as flip chip.

#### Reference



- [1] A. H. Ahmed, A. E. Moznine, D. Lim, Y. Ma, A. Rylyakov and S. Shekhar, "A Dual-Polarization Silicon-Photonic Coherent Transmitter Supporting 552 Gb/s/wavelength," IEEE Journal of Solid-State Circuits, vol. 55, no. 9, pp. 2597-2608, Sept. 2020.
- [2] H. Wakita, M. Nagatani, K. Kurishima, M. Ida and H. Nosaka, "An over-67-GHz-bandwidth 2 Vppd linear differential amplifier with gain control in 0.25-µm InP DHBT technology," in 2016 IEEE MTT-S International Microwave Symposium (IMS), pp. 1-3, 2016.
- [3] A. Zandieh, P. Schvan and S. P. Voinigescu, "57.5GHz bandwidth 4.8Vpp swing linear modulator driver for 64GBaud m-PAM systems," in 2017 IEEE MTT-S International Microwave Symposium (IMS), pp. 130-133, 2017.
- [4] R. J. A. Baker, J. Hoffman, P. Schvan and S. P. Voinigescu, "SiGe BiCMOS linear modulator drivers with 4.8-Vpp differential output swing for 120-GBaud applications," in 2017 IEEE Radio Frequency Integrated Circuits Symposium (RFIC), pp. 260-263, Jun. 2017.
- [5] T. Jyo, M. Nagatani, J. Ozaki, M. Ishikawa and H. Nosaka, "12.3 A 48GHz BW 225mW/ch Linear Driver IC with Stacked Current-Reuse Architecture in 65nm CMOS for Beyond-400Gb/s Coherent Optical Transmitters," in 2020 IEEE International Solid- State Circuits Conference (ISSCC), pp. 212-214, Feb. 2020.